PEMH15; PUMH15

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

Rev. 04 — 15 November 2009

Product data sheet

1. Product profile

1.1 General description

NPN/NPN resistor-equipped transistors.

Table 1. Product overview

Type number			NPN/PNP	PNP/PNP
	NXP	JEITA	complement	complement
PEMH15	SOT666	-	PEMD15	PEMB15
PUMH15	SOT363	SC-88	PUMD15	PUMB15

1.2 Features

- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	50	V
I _O	output current (DC)		-	-	100	mA
R1	bias resistor 1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	



2 of 9

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

Pinning information 2.

Table 3. Pinning

Table 5.	ı ıııınıy		
Pin	Description	Simplified outline	Symbol
1	GND (emitter) TR1		
2	input (base) TR1	6 5 4	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1 R1 R2 S Sym063

Ordering information 3.

Table 4. **Ordering information**

Type number	Package		
	Name	Description	Version
PEMH15	-	plastic surface mounted package; 6 leads	SOT666
PUMH15	SC-88	plastic surface mounted package; 6 leads	SOT363

Marking 4.

Product data sheet

Table 5. **Marking codes**

Type number	Marking code ^[1]
PEMH15	5F
PUMH15	H2*

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	50	V
V_{CEO}	collector-emitter voltage	open base	-	50	V
V_{EBO}	emitter-base voltage	open collector	-	10	V
VI	input voltage				
	positive		-	+30	V
	negative		-	-10	V
Io	output current (DC)		-	100	mA
I _{CM}	peak collector current		-	100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		[1] -	200	mW
	SOT666		[1][2] _	200	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	SOT363		<u>[1]</u> -	300	mW
	SOT666		[1][2]	300	mW

^[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

4 of 9

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

Thermal characteristics 6.

Thermal characteristics Table 7.

. abio ii	Thormal onal actoriotics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> -	-	625	K/W
	SOT666		[1][2] _	-	625	K/W
Per devic	e					
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	SOT363		<u>[1]</u> _	-	416	K/W
	SOT666		[1][2]	-	416	K/W

^[1] Device mounted on a FR4 printed-circuit board, single-sided copper, tin-plated and standard footprint.

Characteristics 7.

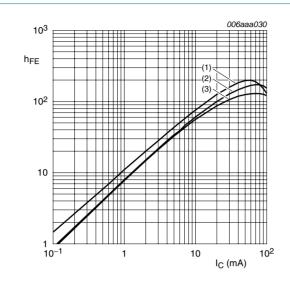
Table 8. **Characteristics**

Product data sheet

 $T_{amb} = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	stor					
I _{CBO}	collector-base cut-off current	$V_{CB} = 50 \text{ V}; I_{E} = 0 \text{ A}$	-	-	100	nA
I _{CEO}	collector-emitter	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	1	μА
	cut-off current	$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	50	μΑ
I _{EBO}	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}$	-	-	0.9	mA
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}$	30	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	-	-	150	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	-	1.1	0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 20 \text{ mA}$	2.5	1.9	-	V
R1	bias resistor1 (input)		3.3	4.7	6.1	kΩ
R2/R1	bias resistor ratio		0.8	1	1.2	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	2.5	pF

^[2] Reflow soldering is the only recommended soldering method.



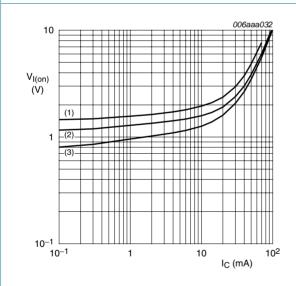
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

DC current gain as a function of collector Fig 1. current; typical values



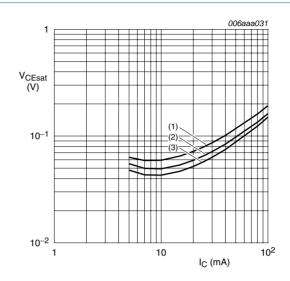
$$V_{CE} = 0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

On-state input voltage as a function of Fig 3. collector current; typical values



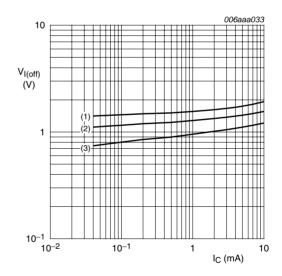
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Collector-emitter saturation voltage as a Fig 2. function of collector current; typical values



$$V_{CE} = 5 V$$

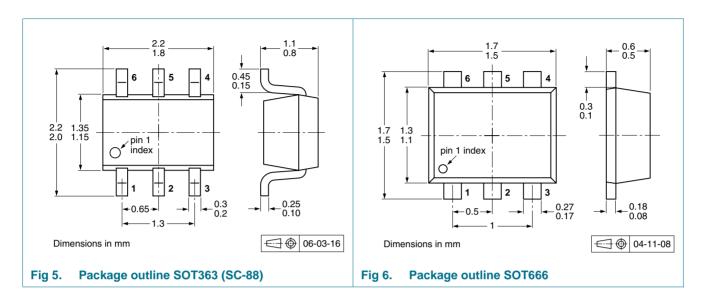
(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = 100 \, ^{\circ}C$$

Off-state input voltage as a function of Fig 4. collector current; typical values

8. Package outline



9. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing of	quantity		
			3000	4000	8000	10000
PEMH15	SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-
		4 mm pitch, 8 mm tape and reel	-	-115	-	-
PUMH15	SOT363	4 mm pitch, 8 mm tape and reel; T1	115	-	-	-135
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165

[1] For further information and the availability of packing methods, see Section 12.

[2] T1: normal taping

[3] T2: reverse taping

7 of 9

NPN/NPN resistor-equipped transistors; R1 = 4.7 k Ω , R2 = 4.7 k Ω

10. Revision history

Table 10. Revision history

Product data sheet

	•			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PEMH15_PUMH15_4	20091115	Product data sheet	-	PEMH15_PUMH15_3
Modifications:	including nev content.	eet was changed to reflect to reflect to was changed to reflect to was legal definitions and disclassing the change outline SOT363 (SC-	aimers. No changes w	
PEMH15_PUMH15_3	20050211	Product data sheet	-	PUMH15_2
PUMH15_2	20040414	Product specification	-	PUMH15_1
PUMH15_1	20031009	Product specification	-	-

11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

11.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

11.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental

damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

11.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

12. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

13. Contents

1	Product profile	1
1.1	General description	1
1.2	Features	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	3
6	Thermal characteristics	4
7	Characteristics	4
8	Package outline	6
9	Packing information	6
10	Revision history	7
11	Legal information	8
11.1	Data sheet status	8
11.2	Definitions	8
11.3	Disclaimers	8
11.4	Trademarks	8
12	Contact information	8
13	Contents	9

Please be aware that important notices concerning this document and the product(s) described herein, have been included in section 'Legal information'.

